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In situ synthesis of C-doped BiVO₄ with natural leaf as a template under different calcination temperatures†

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In this work, a series of C-doped BiVO₄ (BiVO₄-T) with natural leaf structures were synthesized by a dipping-calcination method with the leaf of Chongyang wood seedling as a template under different calcination temperatures. The structures and morphologies of BiVO₄-T were observed by FE-SEM observations. The doped carbon in BiVO₄-T was formed *in situ* from the natural leaf during the calcination process and the amount of doping could be regulated from 0.51–1.16 wt% by controlling the calcination temperature. It was found that the sample calcined at 600 °C (BiVO₄-600) with a C-doping content of 1.16 wt% showed the best photocatalytic degradation activity. After 120 min visible light irradiation, the photocatalytic decomposition efficiency of RhB for BiVO₄-600 is 2.2 times higher than that of no template BiVO₄. The enhanced photocatalytic performance is ascribed to the combined action of the unique morphology and doped-carbon. It is considered that the unique structures and carbon doping of BiVO₄-600 are in favor of the enhancement of visible light absorption, which was supported by UV-vis DRS. Furthermore, the C-doping can enhance the efficient separation and transfer of the photo-generated electron–hole pairs, as proved by PL measurements. This study provides a simple dipping-calcination method and found the best calcination temperature to fabricate a high-performance BiVO₄, which simultaneously achieves morphology and C-doping control in one step.

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1. Introduction

Semiconductor photocatalytic technology has been considered to be an ideal candidate in solving the problem of environmental pollution, owing to its high-performance in degrading and mineralizing organic pollutants.^{1,2} Among various semiconductor photocatalysts, bismuth vanadate (BiVO₄) has received much attention due to its narrow band gap for visible light absorption, low toxicity, low cost, and good stability.^{3–9} Nevertheless, the low charge transportation efficiency of pure BiVO₄ leads to a very poor separation rate of electron–hole pairs, severely hindering its practical applications.^{5,8,10–12}

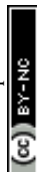
In recent years, researchers have made much effort to improve the charge transportation efficiency of BiVO₄ and enhance its photocatalytic activity.^{4,13–17} Li *et al.* found that depositing noble metals and transition metal oxides on (010) and (110) facets of BiVO₄ single crystals, respectively, can effectively promote the separation rate of photo-generated

carriers.⁴ Besides, Shan *et al.* reported that the BiVO₄/BiOI p–n heterojunction showed significantly enhanced photocatalytic activity for Rhodamine B (RhB) degradation¹⁸ and Zhang *et al.* reported Z-scheme CdS–Au–BiVO₄ with enhanced photocatalytic activity for organic contaminant decomposition.⁵ There are also some efforts of optimizing the structure of BiVO₄ to improve its photocatalytic activity. For example, Fan *et al.* reported an 3D micro/nanoarchitectures BiVO₄, having enhancement of far red to near infrared solar photocatalysis, which was synthesized with butterfly wings as template.¹⁹ Our previous work (Published to *Catal. Sci. Technol.*, <https://doi.org/10.1039/c9cy00475k>, attached to ESI†) synthesized an multi-level structure BiVO₄ by a dipping-calcination method with the leaf of Chongyang wood seedling as template, with the enhancement of the degradation ratio of RhB. In addition, doping with a suitable element, such as C, N, Si, P, Mo *etc.*, is another method to enhance the photocatalytic properties of BiVO₄.²⁰ For example, Xu *et al.* investigated carbon-doped BiVO₄ with enhancement of photocatalytic degradation prepared by a two-step hydrothermal synthesis method using polyvinylpyrrolidone K-30 as a template and L-cysteine as the carbon source.²¹ Yin *et al.* fabricated C-doped BiVO₄ with hierarchical structures by a novel sol–gel method to improve the photocatalytic activity for water oxidation and organic matter degradation.²⁰ In order to simultaneously achieve the structure and C-doping control in one step, we design and fabricate C-doped

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BiVO_4 with natural leaf as template by controlling the calcination temperature.

In this study, a series of C-doped BiVO_4 ($\text{BiVO}_4\text{-}T$) were synthesized by a dipping-calcination method with the leaf of Chongyang wood seedling as template under different calcination temperature. The field emission scanning electron microscopy (FESEM), X-ray diffraction (XRD), thermogravimetric and differential scanning calorimetry analyzer (TG-DSC) and fourier transform infrared spectroscopy (FTIR) were used to characterize the morphology, crystalline structure, the content of carbon doping and chemical composition of the photocatalysts. The UV-vis diffuse reflectance spectroscopy (DRS) and the photoluminescence (PL) spectra were analyzed to investigate the light absorption properties and separation rate of photo-generated carriers of the photocatalysts. Furthermore, the activities of the photocatalysts were evaluated by the RhB photocatalytic degradations under visible light irradiation.

2. Experimental section

2.1 Materials

All chemicals were of analytical grade and used without further purification. 37% hydrochloric acid, 25% glutaraldehyde, $\text{Bi}(\text{NO}_3)_3 \cdot 5\text{H}_2\text{O}$, NH_4VO_3 , glycerol, ethanol and 65% nitric acid, were purchased from Sinopharm Chemical Reagent Co., Ltd., China. Tetramethylammonium hydroxide (TMAH) was purchased from Shanghai Jingchun Industrial Co. Ltd., China.

2.2 Synthesis of photocatalysts

A series of C-doped BiVO_4 were synthesized by a dipping-calcination method^{19,22} with the leaf of Chongyang wood seedling as template. In a typical procedure, the leaves were soaked in 2% glutaraldehyde phosphate buffer at 4 °C for 8 h, immersed in 5% hydrochloric acid for 3 h, and immersed in BiVO_4 impregnation solution for 4 d (0.1 g leaf, 180 mL BiVO_4 impregnation solution), successively. The BiVO_4 impregnation solution was prepared as our previous work (Published to *Catal. Sci. Technol.*, <https://doi.org/10.1039/c9cy00475k>, attached to ESI†). After that, the treated leaf was calcined in air for 6 hours at 400, 450, 500, 550, 600, 650 and 700 °C in a furnace, respectively. Then the obtained catalysts were assigned as $\text{BiVO}_4\text{-}T$ ($\text{BiVO}_4\text{-}400$, $\text{BiVO}_4\text{-}450$, $\text{BiVO}_4\text{-}500$, $\text{BiVO}_4\text{-}550$, $\text{BiVO}_4\text{-}600$, $\text{BiVO}_4\text{-}650$ and $\text{BiVO}_4\text{-}700$).

For comparison, no template BiVO_4 was also synthesized. Put the BiVO_4 impregnation solution (the same as above) into oven to dry at 60 °C for 48 h until the water evaporated

completely. Then calcined the residue at 600 °C for 6 h. After that, no template BiVO_4 was obtained.

2.3 Characterization

The morphologies of the prepared photocatalysts were investigated using a HITACHI SU1080 FE-SEM. The BET surface area was evaluated by a ASAP2020M+C constant volume adsorption apparatus with N_2 adsorption. The XRD measurements were carried out on a Rigaku D/max 2550 VB/PC X-ray diffractometer with Cu K α radiation. The TG-DSC of the samples were detected by a Netzsch STA 449F3 synchronous thermal analyzer. The FTIR spectra were recorded on a Thermo Scientific Nicolet IS50 spectrometer using a 360 nm LED laser as the light source and the detection wavelength was 540 nm. The UV-vis DRS were measured with a SHIMADZU UV-2450 spectrometer equipped with an integrating sphere assembly, using BaSO_4 as the reference material. The PL spectra were recorded on a SHIMADZU RF5301PC by using the 380 nm line of a Xe lamp as the excitation source at room temperature.

2.4 Photocatalytic activity measurements

The photocatalytic activities of the samples were evaluated by the degradations of RhB under visible light irradiation. Briefly, 10 mg catalyst was added in the RhB solution (150 mL, 10 mg L^{-1}). A 350 W Xe lamp (Shenzhen Stone-lighting Opto Device Co., Ltd., China) was used as a simulated solar light source. Before turning on the light, the suspension was stirred for 60 min in the dark to obtain the adsorption-desorption equilibrium of the RhB on the surface of the photocatalyst. Then, the suspension was irradiated by the lamp under magnetic stirring. In the course of the reaction, withdrawing 2 mL suspension from the reaction vessel every 20 min. And then, removed the photocatalyst from the suspension by centrifugation. Finally, the concentration of RhB in the solution was monitored using a UV-vis spectrophotometer (SHIMADZU UV-2450).

3. Results and discussion

3.1 Characterization of catalysts

3.1.1 Morphology analysis. The macroscopic morphology of the series of C-doping BiVO_4 and no template BiVO_4 are illustrated in Fig. 1. Compared with the powdered form of no template BiVO_4 , the appearance of all the C-doping BiVO_4 exhibit the natural leaf's shape and the overall color gradually deepened with the increase of calcination temperature, which

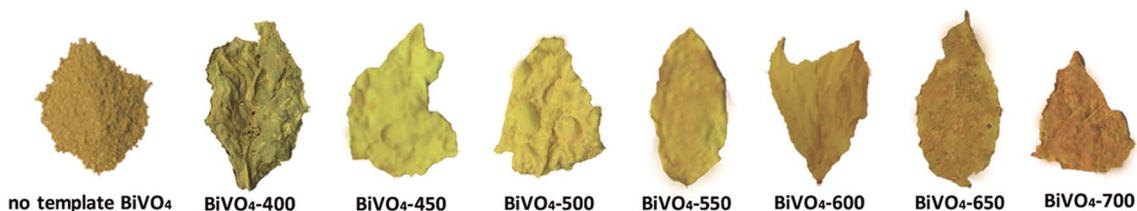


Fig. 1 The macrophotograph of no template BiVO_4 , $\text{BiVO}_4\text{-}400$, $\text{BiVO}_4\text{-}450$, $\text{BiVO}_4\text{-}500$, $\text{BiVO}_4\text{-}550$, $\text{BiVO}_4\text{-}600$, $\text{BiVO}_4\text{-}650$ and $\text{BiVO}_4\text{-}700$.



Table 1 The carbon-doping contents and specific surface area of BiVO₄-T and no template BiVO₄

Catalyst	BiVO ₄ -400	BiVO ₄ -450	BiVO ₄ -500	BiVO ₄ -550	BiVO ₄ -600	BiVO ₄ -650	BiVO ₄ -700	No template BiVO ₄
Carbon contents (wt%)	0.51	0.64	0.72	0.89	1.16	1.01	0.84	0
Specific surface area (m ² g ⁻¹)	5.12	4.23	3.28	2.14	2.06	1.23	0.89	0.32

may be owing to the different amount of C-doping. In order to verify the carbon content, TG-DSC was carried out and the results are shown in Table 1. The C-doping content is increase from BiVO₄-400 at 0.51 wt% to BiVO₄-600 at 1.16 wt% and slightly decline when the calcination temperature exceeds 600 °C.

At the micro-level, the morphologies of C-doped BiVO₄ and no template BiVO₄ were observed by FE-SEM, shown in Fig. 2. In Fig. 2, compared with the cluttered distribution of BiVO₄ grain crystal for no template BiVO₄, the C-doped BiVO₄-T show the regular porous structures, which inherited from natural leaf's structure (the more leaf-like structures has been observed in our precious work which has been published to *Catal. Sci.*

Technol., <https://doi.org/10.1039/c9cy00475k>, attached to ESI†). Moreover, from BiVO₄-400 to BiVO₄-700, the size of the crystallites gradually increase and the surface area (shown in Table 1) gradually decrease, illustrating that rising calcination temperature can make the grain size increase.

3.1.2 XRD analysis. The XRD of the different samples were analyzed to determine their crystallographic structures. Fig. 3 was the XRD patterns of the samples. As shown in Fig. 3A, all the catalysts exhibit the characteristic peaks of monoclinic scheelite phase BiVO₄ (JCPDS file: 14-0688),^{12,23,24} implying that with increase in calcining temperature from 400 to 700 °C, the main crystalline phase of all the samples were monoclinic scheelite phase BiVO₄. It is worth noting that in the XRD pattern of

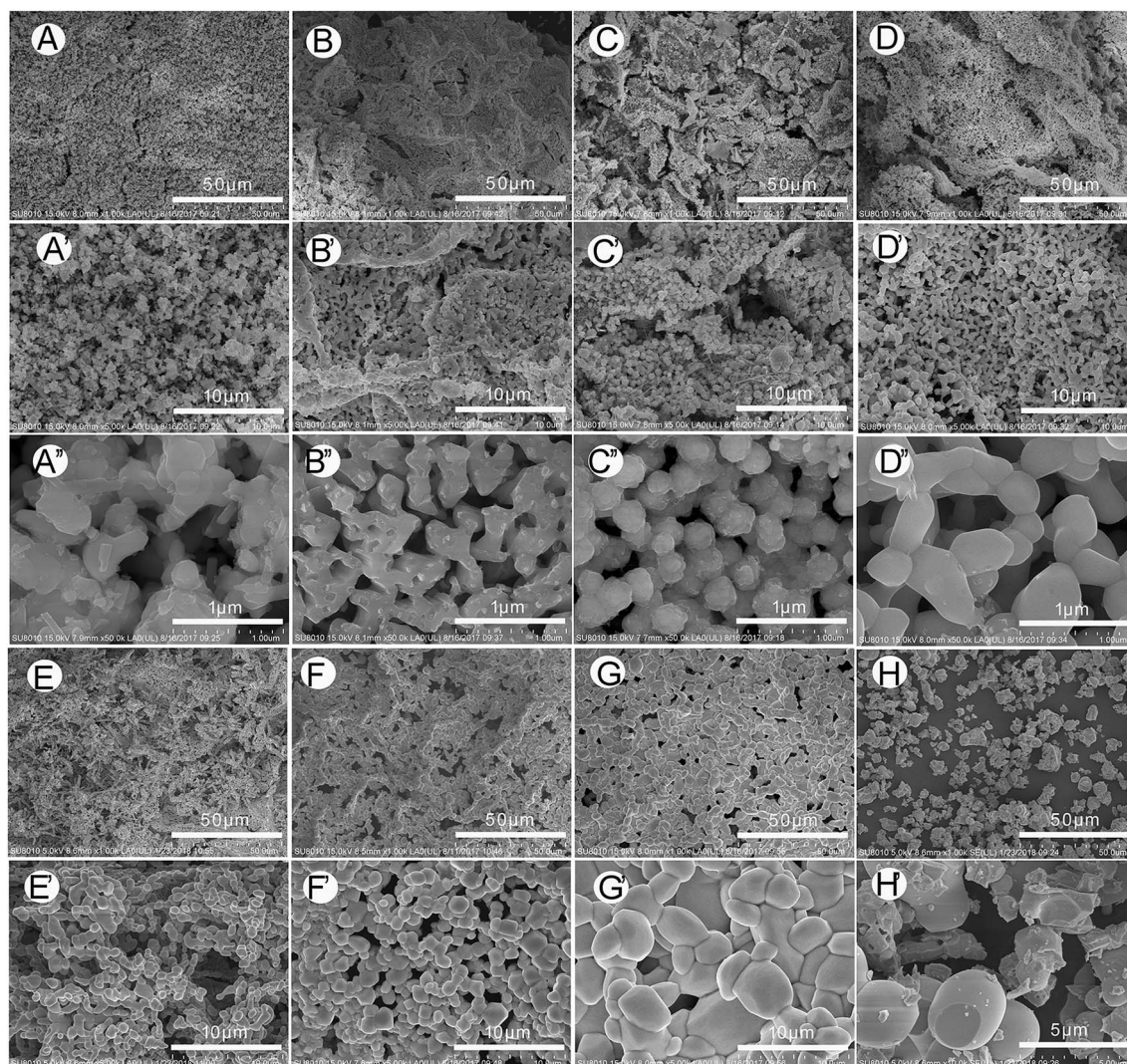


Fig. 2 FE-SEM images of BiVO₄-400 (A, A' and A''), BiVO₄-450 (B, B' and B''), BiVO₄-500 (C, C' and C''), BiVO₄-550 (D, D' and D''), BiVO₄-600 (E and E'), BiVO₄-650 (F and F'), BiVO₄-700 (G and G') and no template BiVO₄.



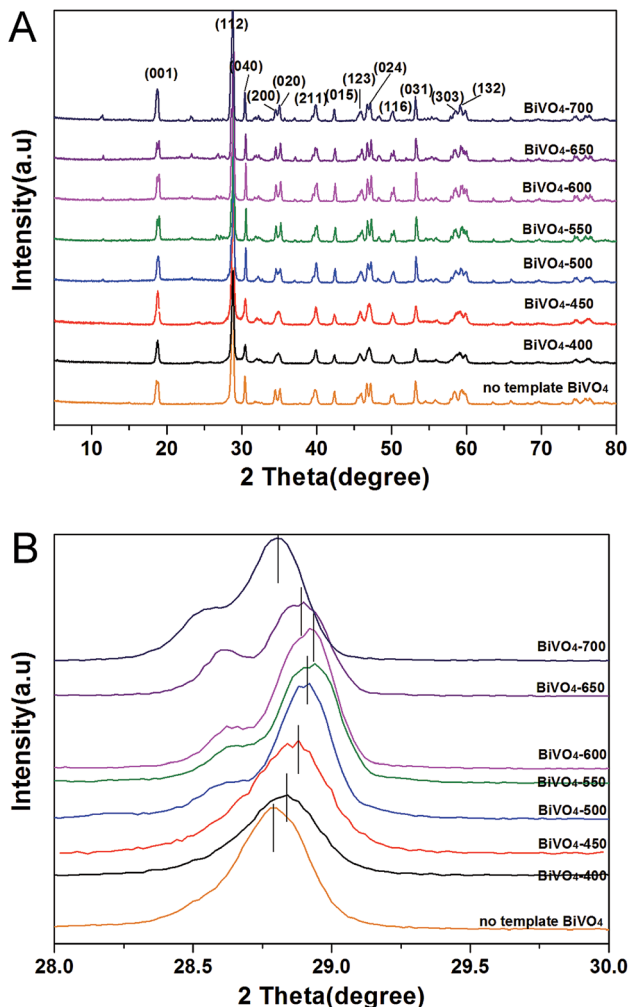


Fig. 3 XRD patterns (A) and magnified peaks of (112) planes in the range of 2θ from 28° to 30° (B) of no template BiVO_4 , BiVO_4 -400, BiVO_4 -450, BiVO_4 -500, BiVO_4 -550, BiVO_4 -600, BiVO_4 -650 and BiVO_4 -700.

BiVO_4 -500, BiVO_4 -550, BiVO_4 -600, BiVO_4 -650 and BiVO_4 -700, there are some small peaks at a degree of 12, 23, 26, 38, 48, which can be assigned to the impurity phase $\text{Bi}_4\text{V}_2\text{O}_{11}$ (JCPDS file: 42-0135).²⁵ This result illustrates that when the calcination temperature reaches 500°C , there will be some impurity phases. $\text{Bi}_4\text{V}_2\text{O}_{11}$ is an orthogonal compound, mainly a thermoelectric, ferroelectric material, and its photocatalytic performance is poor, mainly because its 3.05 eV band gap is difficult to excite in the visible range.²⁵ Fig. 3B shows a magnified view of (112) diffraction peaks, which exhibits gradual shifts to higher angles with the increase of calcination temperature and the peak drops back a little when the temperature exceed 600°C . The maximum shifting of 0.125° is reached at BiVO_4 -600, which having the largest amount of C-doping. Compared with (112) diffraction peak of no template BiVO_4 , the peak of all the BiVO_4 -T show higher angle shift. These result may be attributed to the lattice expansion owing to the slight part of carbon atom doping, and illustrates that C may have a certain influence on the $d(112)$ spacings of the BiVO_4 . It

is considered that element doping is favor of the enhancement of photocatalytic activity for the incremental reactive sites and promoted electron-hole separation efficiency.²⁶

3.1.3 FTIR spectra analysis. The FTIR spectra of BiVO_4 -T and no template BiVO_4 are shown in Fig. 4. In the FTIR spectrums of all the samples, the absorption peaks at 475 , 570 , 736 – 744 and 840 – 845 cm^{-1} are corresponding to the typical symmetrical stretching vibration of VO_4^{3-} , stretching vibration of Bi–O, deformation bending vibration of V–O and symmetrical stretching vibration of V–O, respectively.^{27,28} All absorption peaks at 3445 cm^{-1} are attributed to the stretching vibrations of the adsorbed H_2O . The absorption peak of BiVO_4 -T at 1100 cm^{-1} is assigned to the typical antisymmetric stretching vibration of Si–O–Si,²⁹ while the peak is not appear in the FTIR spectra of no template BiVO_4 , illustrating that the original Si element in the natural leaf doped into BiVO_4 -T. Moreover, other methods has also been used to confirm the existence of Si, such as EDS (attached to the ESI†) and XPS (in our previous work, which has been published to *Catal. Sci. Technol.*, <https://doi.org/10.1039/c9cy00475k>, attached to ESI†).

3.1.4 UV-vis DRS analysis. The light absorption properties of the samples were analysed *via* UV-vis DRS, as shown in Fig. 5A. All of the samples have obvious absorption in range of visible light. For BiVO_4 -400, BiVO_4 -450, BiVO_4 -500, BiVO_4 -550 and BiVO_4 -600, the absorption edge shows redshifts, while in case of BiVO_4 -600, BiVO_4 -650 and BiVO_4 -700 there are blueshifts of the absorption edge. This regular change indicates that the band-gap energy of BiVO_4 -T was affected by the calcination temperature, which is caused probably by the C doping. Moreover, the absorption edge of all C-doping BiVO_4 -T show redshifts, compared with no template BiVO_4 . This result may be attributed to the unique structures and C doping of BiVO_4 -T.

The optical band gap of a semiconductor can be estimated according to the following formula:^{29,30}

$$(\alpha hv) = A(hv - E_g)^{n/2}$$

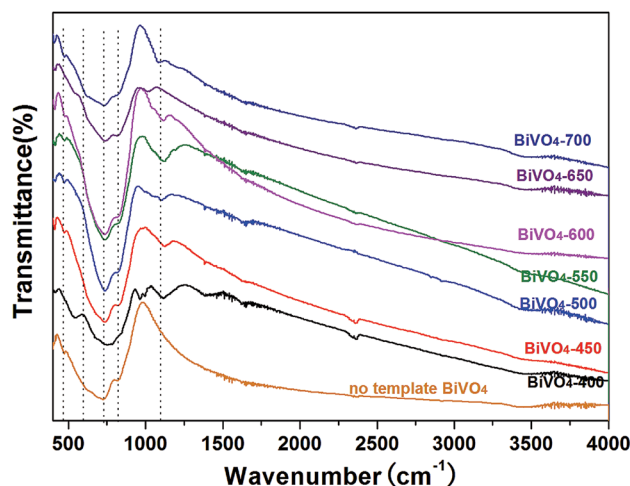


Fig. 4 FTIR spectra of no template BiVO_4 , BiVO_4 -400, BiVO_4 -450, BiVO_4 -500, BiVO_4 -550, BiVO_4 -600, BiVO_4 -650 and BiVO_4 -700.



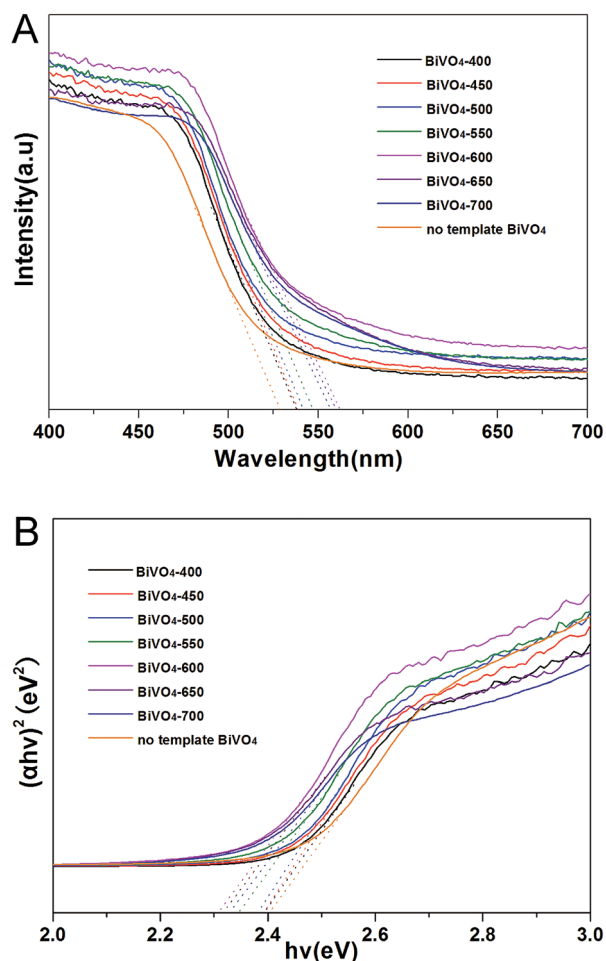


Fig. 5 (A) UV-vis DRS spectra of no template BiVO₄, BiVO₄-400, BiVO₄-450, BiVO₄-500, BiVO₄-550, BiVO₄-600, BiVO₄-650 and BiVO₄-700. (B) The calculation diagram of band gaps for no template BiVO₄, BiVO₄-400, BiVO₄-450, BiVO₄-500, BiVO₄-550, BiVO₄-600, BiVO₄-650 and BiVO₄-700.

where α , h , ν , A and E_g are absorption coefficient, Planck's constant, light frequency, constant value and band gap energy, respectively. Due to BiVO₄ are direct transition type of semiconductors, the direct band gaps of BiVO₄ can be calculated according to the plots of $(\alpha h\nu)$ and *versus* $(h\nu)$ (shown in Fig. 5B). Therefore, the band gap energy of no template BiVO₄, BiVO₄-400, BiVO₄-450, BiVO₄-500, BiVO₄-550, BiVO₄-600, BiVO₄-650 and BiVO₄-700 are determined to be 2.38, 2.40, 2.39, 2.38, 2.35, 2.31, 2.32 and 2.33 eV, respectively. It is clear that the banding gap energy shows a systematic decrease with the C doping level. Choi³¹ thought the electronic structure of the C–V bond and C–W bond are similar. Houston *et al.*³² used to characterize the density state of the unfilled parts of the C–W guide band and found that the unfilled part of d orbit of C–W semiconductor is extending. In this work, there is a C–V bond in the catalyst, which has been confirmed in our previous work (Published to *Catal. Sci. Technol.*, <https://doi.org/10.1039/c9cy00475k>, attached to ESI[†]). Owing to the strong interaction between the orbit of V 3d and the C 2p, the minimum value of the guide band is further reduced, which is beneficial to the absorption of visible light.

3.1.5 PL analysis. Fig. 6 shows the PL spectra of BiVO₄-T and the no template BiVO₄. As shown in Fig. 6, all of the samples exhibit a strong PL emission peak around 540 nm, which can be attributed to the recombination of electro-hole pairs. The intensity of the peak gradually weakens with the calcining temperatures increasing from 400 to 600 °C, while, as the temperature continues to increase from 650 to 700 °C, the intensity of the peak gradually enhances. In addition, compared with no template BiVO₄, all of the C-doped BiVO₄-T exhibit weaker PL intensity. The similar phenomena have also been observed in our previous studies,^{3,33,34} which may be due to the doping of carbon element in favor of rapid electron transfer. Wang *et al.*³⁵ investigated the temporal evolution of fluorescence from carbon nanotubes and pointed out low fluorescence quantum yield originated from the rapidly quenching fluorescence rather than from the inherent weakness of the radiative transitions. Just because of high electron mobility, carbon affords the quick electron transfer resulting in the decrease of the emission intensity.

3.2 Photocatalytic activity

The photocatalytic activities of the samples were evaluated in terms of the degradations of RhB under visible light irradiation and shown in Fig. 7. For comparison, the blank experiment (no catalyst) was also performed. This result can exclude the effects of self-degradation of RhB under visible-light irradiation. After visible light irradiation for 2 h, the degradation ratio of RhB gradually increases from BiVO₄-400 at 47% to BiVO₄-600 at 82%. While, as the temperature continues to increase from 650 to 700 °C, the degradation ratio of RhB decreases slightly. BiVO₄-600 has the highest photocatalytic activity, suggesting that a calcination temperature of 600 °C is optimized for the C-doped BiVO₄ photocatalyst.

It is generally considered that the catalytic performance is affected by morphology, crystallographic structure, chemical

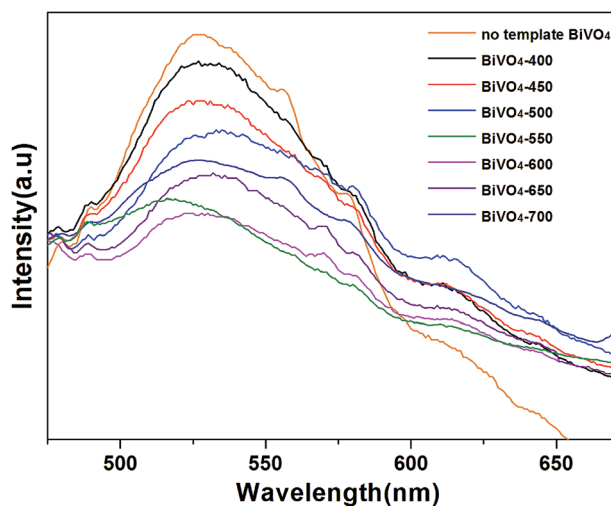


Fig. 6 PL spectra of no template BiVO₄, BiVO₄-400, BiVO₄-450, BiVO₄-500, BiVO₄-550, BiVO₄-600, BiVO₄-650 and BiVO₄-700.



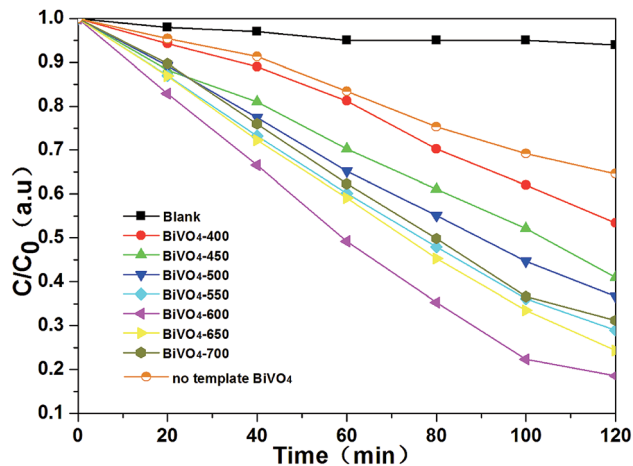


Fig. 7 Photocatalytic degradations of RhB over blank, no template BiVO₄, BiVO₄-400, BiVO₄-450, BiVO₄-500, BiVO₄-550, BiVO₄-600, BiVO₄-650 and BiVO₄-700.

composition, light absorption properties, and separation efficiency of the photo-generated electron-hole pairs of the semiconductor photocatalyst. However, in this work, with the increasing of calcining temperature, the morphology of the samples gradually deteriorate (the particle size gradually increase and the surface area gradually decrease), the crystallographic structures of all the samples were not changed (all the catalysts are monoclinic scheelite phase BiVO₄). Obviously, neither morphology nor crystallographic structures of the samples influences the photocatalytic activity. Comprehensively analyzing the photocatalytic activities of the photocatalysts and the UV-vis DRS and PL results, we can get that it is coincident that the regularities of the change of photocatalytic activities, the absorption edge and the separation efficiency of the photo-generated electron-hole pairs. Furthermore, according to the UV-vis DRS and PL analysis, all of the influence factor can be attribute to carbon element doping. With the rising of calcining temperature, the amount of doped carbon element increases and reaches optimum at 600 °C, BiVO₄-600 has the highest activity. While with the continually rise of calcining temperature, the amount of doped carbon element decreases, and the photocatalytic activity decreases with it. Therefore, The effect of calcination temperature on the catalytic activity of BiVO₄-T is mainly due to the influence of carbon doping content in the catalyst.

4. Conclusions

In this work, a series of C-doped BiVO₄ with natural leaf structures were synthesized by a dipping-calcination method with the leaf of Chongyang wood seedling as template under the calcination temperature of 400, 450, 500, 550, 600, 650 and 700 °C, respectively. The fine replication of natural leaf's macroscopic morphology and microstructure was confirmed directly by macrophotograph and FE-SEM. With the rise of calcination temperature, the carbon content of BiVO₄-T increase from BiVO₄-400 at 0.51 wt% to BiVO₄-600 at 1.16 wt%,

while when the temperature exceed 600 °C, the carbon content drops back a little. The carbon doped into BiVO₄ crystal and induces lattice expansion. The measured photocatalytic activity results illustrate that BiVO₄-600 with a C-doping content of 1.16 wt% showed the best photocatalytic degradation activity. After 120 min visible light irradiation, the photocatalytic decomposition efficiency of RhB for BiVO₄-600 is 2.2 times higher than that of no template BiVO₄. The improved photocatalytic performance is ascribed to not only the leaf-like structures but also the *in situ* doped-carbon, enhancing the visible light absorption ability as well as improving the separation of photo-generated electron-hole pairs. This study provides a simple dipping-calcination method and found the best calcination temperature to fabricate a high-performance BiVO₄, which simultaneously achieve the morphology and C-doping control in one step.

Conflicts of interest

There are no conflicts to declare.

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